Interface Modification of Inverted Bulk Heterojunction Organic Solar Cell by ZnO and CuO\textsubscript{x} Layers

Muhammad Tanveer*, Amir Habib, Muhammad Bilal Khan

School of Chemical and Materials Engineering, National University of Sciences and Technology, Islamabad 44000, Pakistan

Center for Energy Systems, National University of Sciences and Technology, Islamabad 44000, Pakistan

*Corresponding author: email address; mtanveerp@scme.nust.edu.pk

Abstract

The enhanced performance of the poly(3-hexylthiophene) (P3HT) and [6,6]-phenyl C61-butyric acid methyl ester (PCBM) bulk heterojunction devices was achieved by interface modification with solution processed ZnO and CuO interlayer. The highest power conversion efficiency (PCE) of 4.24±0.01\% was achieved by optimizing the thickness of the interface layers by varying spin coating speeds. The thin CuO layer improved both the short circuit current density (12.23mA/cm\textsuperscript{2}) and fill factor (0.62) by providing additional light absorption through redistributing the electric field within the active layer. The incident photon to current conversion efficiency (IPCE) was also improved to 67\% by a 15nm thick CuO interlayer, showing that maximum carriers can be generated by optimizing the thickness of the amorphous CuO layer. The fabricated devices were characterized under 100mW/cm\textsuperscript{2} illumination and optical properties of each layer were also investigated.

Keyword: Organic solar cell, Interface modification, ZnO and CuO layers

Introduction

The development of bulk heterojunction (BHJ) organic photovoltaic (OPV) devices has attracted more attention due to their potential advantages like low cost, flexibility, and large scale fabrication possibilities [1-6]. The regular structure of an OPV device is composed of a photoactive layer formed by a blend of an electron donor conjugated polymer and an electron acceptor fullerene derivatives. The active layer is sandwiched between two electrodes; anode is usually indium doped tin oxide (ITO) and cathode is a low work function metal cathode like Al [3,4,7]. Poly(3,4-ethylene dioxythiophene): (polystyrene sulfonic acid) (PEDOT:PSS) is most widely used interface material between ITO and active layer in regular structure. The device performance of this kind of structure is often degraded both by the instability of the PEDOT:PSS interface and oxidation of the cathode[8,9]. These challenges were addressed in the regular OPV device structure by inverting the device structure by replacing the low work function top electrode with a high work function metal electrode where electrons are accepted by ITO[10-12]. The inverted structure has improved device lifetime due to removal of PEDOT:PSSas its acidic nature always causes device instability. The other advantage of inverted configuration is vertical phase separation in BHJ which improved performance of the device[13]. The challenge in inverted devices is the selection of the electron accepting material and device design, so that this layer will not only affect the absorption of solar spectrum but also collect electrons and block holes efficiently. The energy level alignment in this regard is very crucial. There are various reports where diverse materials are used as an electron accepting material. The mostly used are zinc oxide (ZnO) [14-16], titanium oxide (TiO\textsubscript{x}) [17-20], cesium carbonate (Cs\textsubscript{2}CO\textsubscript{3})[21-24] and lithium fluoride (LiF)[25]. The interface layer of these materials is deposited by atomic layer deposition (ALD)[26,27], and sol–gel[28] techniques. The sol-gel process has the advantage of the solution process and low cost as no high temperature and vacuum are essential for the process.

The performance of the inverted OPV devices has lowered due to reflection losses. These barriers are lowered by introducing a thin metal oxide interface layer between the active layer and the top electrode. This study has focussed on the optimization of the thickness of the CuO\textsubscript{x} interlayer for improved performance of inverted P3HT:PCBM BHJ devices. The various parameters like viscosity of the CuO\textsubscript{x} sol and annealing temperature of the amorphous CuO\textsubscript{x} layer was also optimized.

Synthesis of ZnO and CuO\textsubscript{x} layers

ZnO solution was spin coated on ITO, which plays both roles- as an electron accepting layer and a hole blocking layer. The solution was prepared by dissolving 0.7M zinc acetate dehydrate in 2-methoxy ethanol, while 4\% MEA was added during the stirring process at 60\(^\circ\)C for two hours to get a homogenous solution. This solution was spin coated on ITO at 2800rpm for 35s, dried to hydrolysis at RT for one hour and then annealed at 400\(^\circ\)C for 5min. The spin coating conditions were optimized to get 25-40nm thin ZnO interface layer.

CuO\textsubscript{x} solution was prepared by stirring a mixture of (0.25M) copper (II) acetate monohydrate dissolved in (99\%) isopropyl alcohol (IPA) and (1\%) deionized water at 50\(^\circ\)C for three hours. The solution was spin coated on active layer at various spin coating speeds for 35s, followed by annealing at 150\(^\circ\)C for 10min.
Photovoltaic Devices Fabrication

The schematic and energy band diagram is shown in Figure 1. A 260nm thick photo-active layer was spin coated by P3HT:PCBM blend at 800rpm for 30s on the ZnO/ITO substrate. The blend solution was obtained by dissolving (20mg/ml) P3HT and (15mg/ml) PCBM in chlorobenzene. An optimum blend ratio (1:1) was used in this particular study to obtain minimum P3HT grain size for maximum exciton dissociation in the active layer.

The thickness of the CuO layer on top of active layer was optimized by various spin coating speeds. Firstly, the solution was spin coated at 1200rpm to get 60nm thick CuOx layer. Then the second device was fabricated by spin coating the solution on active layer at 1500rpm. The thickness of this layer was 35nm. The other devices were fabricated by spin coating CuO solution at 1800rpm, 2100rpm and 2500rpm. The thickness of the resultant spacer layers were 20nm, 15nm and 10nm, respectively. Ag was thermally evaporated as the top electrode on CuO optical spacer to complete the device structure. The various layers of the fabricated devices are shown by FE-SEM in Fig2.

Results and Discussions

The high mobility metal oxide thin film provides enhanced carrier transport as compared to organic material. The crystalline homogenous film of ZnO was obtained after annealing at 400°C and confirmed by XRD analysis. The amorphous CuO film on top of active layer act as an optical spacer. The XRD analysis of CuO has shown that the film is crystalline after annealing above 450°C.

The absorption and transmission spectra of ZnO indicate that most of the light in the visible region has been allowed to be incident on the active layer, as shown in Fig 3. The maximum absorption by the blend is in the wavelength range of 475nm to 575nm and in this range the transmission by ZnO is more than 92%. On the other hand, better absorption below 400nm by this layer has a positive effect on device performance by contributing increased generated carrier through absorption within this wavelength range. The CuO optical spacer has 85% transmission in the wavelength range above 400nm.

The photo-induced charge separation at the nano scale interface of the junction between the P3HT and PCBM occurs in sub-picosecond time – [7,29]. The photo luminescence spectroscopy, showing greatly quenched photo luminescence by P3HT:PCBM blend (Figure 4(a), and Figure 4©), and evidencing the enhancement of photoconductivity. The exciton quenching attributed by low luminescence intensity on introduction of CuO optical spacer shows that excitons are dissociated at blend CuOx interface.

The J-V characteristic of the fabricated devices is shown in Figure 5. The effective work function of ITO and metal has been tuned by the application of ZnO and CuO inter layers respectively [30], which controlled the charge extraction from the active layer and therefore, short circuit current density (Jsc). The Jsc of the devices fabricated with CuOx spin coated at 1200rpm is minimum (8.22mAcm⁻²). The Jsc increased to a maximum (12.23mAcm⁻²) for the devices which were spin coated at 2100rpm by CuOx. The increase in
As the rpm of optical spacer exceeds 2500 rpm, $J_0$ was lowered. The possible explanation could be the penetration of the top electrode into the active layer as thin optical spacer has reduced protection from the damage during contact deposition. The increased thickness of the optical spacer on the other hand has also increased the series resistance, which reduced $J_0$, as observed for low rpm coated optical spacer.

The open circuit voltage ($V_{oc}$) of the devices fabricated with high rpm CuO was reduced to 0.55 V compared to devices fabricated with thick spacer layer (1200 rpm), having $V_{oc}$ 0.58 V. The introduction of interface layer influences the energy level alignment at organic-organic and organic-electrode interfaces [31-33] by introducing additional energy step. Therefore, the variation in $V_{oc}$ can be attributed to the Fermi level pinning at the polymer-electrode interface.

The fill factor (FF) has improved from 0.58 to 0.62 as optical spacer thickness was reduced by higher rpm. The FF mainly depends upon the morphology of the active layer and the series resistance of the devices [34-36]. The thicker optical spacer increased series resistance of the devices which has reduced the FF.

$J_0$ is due to maximum carrier contribution when the thickness of the CuO optical spacer completely redistributes the light distribution. However, as the rpm of optical spacer exceeds 2500 rpm, $J_0$ was lowered. The possible explanation could be the penetration of the top electrode into the active layer as thin optical spacer has reduced protection from the damage during contact deposition. The increased thickness of the optical spacer on the other hand has also increased the series resistance, which reduced $J_0$, as observed for low rpm coated optical spacer.

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**Figure 5:** The $J$-$V$ characteristic of the inverted organic photovoltaic devices fabricated with CuO, spin coated at different rpm.
The power conversion efficiency (PCE) of the devices was/is also improved by the introduction of ZnO thin layer on ITO, as the crystalline nature of this layer supports the electrons to reach the cathode quickly due to high mobility of ZnO. Whenever only cathode of the device is modified by high mobility metal oxide then there is possibility of space charge due to mobility difference of electron and hole in metal oxide and polymer respectively. In order to overcome this challenge the introduction of metal oxide like CuO is a good choice. The PCE has improved to 4.24±0.01% by spin coating CuO layer with a spin coating speed of 2100rpm on top of the photo-active layer. The structure of various fabricated devices and their respective parameters are presented in Table 1. The major contribution to the efficiency improvement is by J_sc and FF.

Figure 6 shows the incident photon to current conversion efficiency (IPCE) of devices fabricated by CuO optical spacer also act as a hole transport layer spincoated with different spin coating speed. 15nm thick CuO optical spacer spincoated at 2100rpm devices reached up to 67% at 530nm. However, thin optical spacer (10nm) reduced IPCE to 58% though it is much higher than 35% shown by low rpm (1200rpm) coated optical spacer. The increased IPCE is evidenced the increased photogenerated carrier contribution by a spacer layer through redistributing the field inside the active layer and by providing an efficient interface between the anode and active layer.

Table 1: The structure and the parameters of the fabricated inverted organic solar cells.

<table>
<thead>
<tr>
<th>Device structure</th>
<th>Voc (V)</th>
<th>Jsc (mAcm^{-2})</th>
<th>FF</th>
<th>η (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>ITO/ZnO/P3HT:PCBM/CuO_{x} (1200rpm)/Ag</td>
<td>0.58</td>
<td>8.22</td>
<td>0.58</td>
<td>2.68±0.01</td>
</tr>
<tr>
<td>ITO/ZnO/P3HT:PCBM/CuO_{x} (1500rpm)/Ag</td>
<td>0.56</td>
<td>10.82</td>
<td>0.61</td>
<td>3.71±0.02</td>
</tr>
<tr>
<td>ITO/ZnO/P3HT:PCBM/CuO_{x} (1800rpm)/Ag</td>
<td>0.56</td>
<td>11.97</td>
<td>0.62</td>
<td>4.16±0.01</td>
</tr>
<tr>
<td>ITO/ZnO/P3HT:PCBM/CuO_{x} (2100rpm)/Ag</td>
<td>0.56</td>
<td>12.23</td>
<td>0.62</td>
<td>4.24±0.01</td>
</tr>
<tr>
<td>ITO/ZnO/P3HT:PCBM/CuO_{x} (2500rpm)/Ag</td>
<td>0.55</td>
<td>9.58</td>
<td>0.62</td>
<td>3.28±0.03</td>
</tr>
</tbody>
</table>

Conclusions

The performance of the P3HT:PCBM BHJ devices was improved by interface modification with solution processed ZnO and CuO interlayer. The highest PCE achieved (4.24±0.01%) by optimizing the thickness of the CuO interlayer at a spin coating speeds of 2100rpm. The thin CuO layer improved both the short circuit current density (12.23mA/cm²) and fill factor (0.62). The improved performance is attributed to the additional light absorption through redistributing the electric field within the active layer. The IPCE has also improved to 67% by a 15nm thick CuO interlayer, showing that maximum carriers can be generated and effectively collected by optimizing the thickness of the amorphous CuO layer.

Acknowledgments

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References
